



45V PNP SMALL SIGNAL TRANSISTOR IN DFN0806

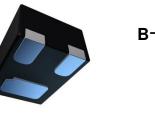
Features

- $BV_{CEO} > -45V$
- I_C = -100mA High Collector Current
- P_D = 435mW Power Dissipation
- 0.48mm² Package Footprint, 16 times smaller than SOT23
- 0.4mm Height Package Minimizing Off-Board Profile
- Complementary NPN Type BC847BFA
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

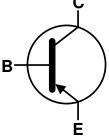
Mechanical Data

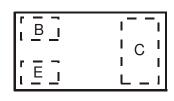
- Case: X2-DFN0806-3
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish NiPdAu, Solderable per MIL-STD-202, Method 208 e4
- Weight: 0.0008 grams (Approximate)





Bottom View





Device Symbol

Top View **Device Schematic**

Ordering Information (Note 4)

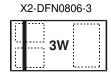
Top View

Product	Marking	Reel size (inches)	Tape width (mm)	Quantity per reel
BC857BFA-7B	3W	7	8mm	10.000

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
- 2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + CI) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

Marking Information



Top View Bar Denotes Base and Emitter Side

3W = Product Type Marking Code

Absolute Maximum Ratings (@TA = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V_{CBO}	-50	V
Collector-Emitter Voltage	V _{CEO}	-45	V
Emitter-Base Voltage	V_{EBO}	-6.0	V
Continuous Collector Current	Ic	-100	mA
Peak Pulse Collector Current	I _{CM}	-200	mA



Thermal Characteristics (@TA = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Power Dissipation (Note 5)	P _D	435	mW
Thermal Resistance, Junction to Ambient (Note 5)	$R_{\theta JA}$	287	°C/W
Thermal Resistance, Junction to Lead (Note 6)	$R_{ heta JL}$	150	°C/W
Operating and Storage and Temperature Range	T _J , T _{STG}	-55 to +150	°C

ESD Ratings (Note 7)

Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge - Human Body Model	ESD HBM	4,000	V	3A
Electrostatic Discharge - Machine Model	ESD MM	200	V	В

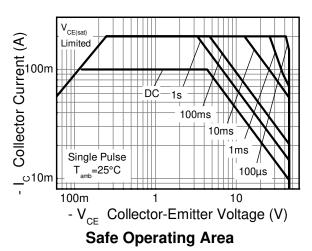
Notes:

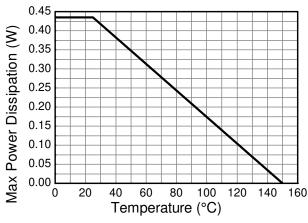
5. For the device mounted on minimum recommended pad layout 1oz copper that is on a single-sided 1.6mm FR4 PCB; device is measured under still air conditions whilst operating in steady state condition. The entire exposed collector pad is attached to the heatsink.

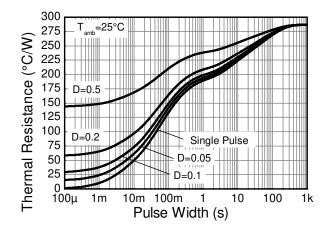
100

- 6. Thermal resistance from junction to solder-point (on the exposed collector pad).
- 7. Refer to JEDEC specification JESD22-A114 and JESD22-A115.

Thermal Characteristics and Derating Information



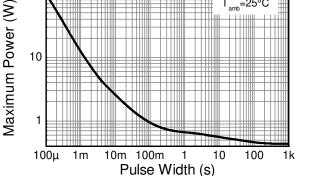




Derating Curve

Single Pulse

May 2017



Transient Thermal Impedance

Pulse Power Dissipation



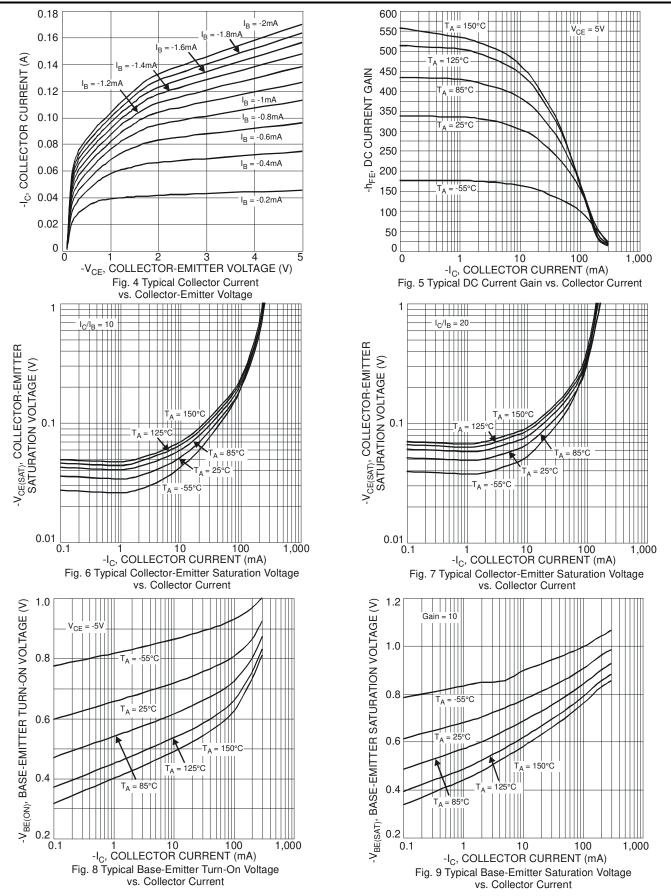
Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typical	Max	Unit	Test Condition
OFF CHARACTERISTICS						
Collector-Base Breakdown Voltage	BV _{CBO}	-50	-100	_	٧	$I_C = -50\mu A, I_B = 0$
Collector-Emitter Breakdown Voltage	BV _{CES}	-50	-90	_		$I_C = -50\mu A, I_B = 0$
Collector-Emitter Breakdown Voltage (Note 8)	BV _{CEO}	-45	-65	_	V	$I_{C} = -1 \text{mA}, I_{B} = 0$
Collector-Base Breakdown Voltage	BV _{EBO}	-6.0	-8.5	_	V	$I_E = -50\mu A, I_C = 0$
Collector-Base Cut-Off Current	I _{CBO}	_	_	-15	nA	V _{CB} = -40V
Collector-Emitter Cut-Off Current	I _{CES}	_	_	-15	nA	V _{CE} = -40V
ON CHARACTERISTICS (Note 8)						
DC Current Gain	hee	200	340	_	_	$I_C = -10\mu A$, $V_{CE} = -5.0V$
Do Guiterit Gairi	h _{FE}		330	470		$I_C = -2.0 \text{mA}, V_{CE} = -5.0 \text{V}$
Collector-Emitter Saturation Voltage	V "	sat) —	-70	-175 -500	mV	$I_C = -10mA$, $I_B = -0.5mA$
Concetor Emitter Cataration Voltage	V _{CE(sat)}		-300			$I_C = -100 \text{mA}, I_B = -5.0 \text{mA}$
Base-Emitter Saturation Voltage	$V_{BE(sat)}$	_	-760	-1,000 m\/	mV	$I_C = -10mA$, $I_B = -0.5mA$
Dase Emilier Galaration Voltage	V BE(sat)		-885	-1,100	111.4	$I_C = -100 \text{mA}, I_B = -5.0 \text{mA}$
Base-Emitter Voltage	V _{BE(on)}	-600	-670	-780	mV	$I_C = -2.0 \text{mA}, V_{CE} = -5 \text{V}$
		_	-715	-850		$I_C = -10 \text{mA}, V_{CE} = -5 \text{V}$
SMALL SIGNAL CHARACTERISTICS						
Output Capacitance	C_{obo}		2.0	—	pF	$V_{CB} = -10.0V$, $f = 1.0MHz$, $I_{E} = 0$
Current Gain-Bandwidth Product	f⊤	100	340		MHz	$V_{CE} = -5V$, $I_{C} = -10mA$, $f = 100MHz$

Notes: 8. Measured under pulsed conditions. Pulse width $\leq 300 \mu s$. Duty cycle $\leq 2\%$.



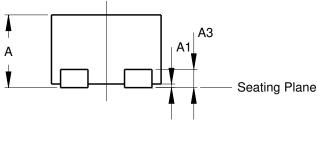
Typical Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

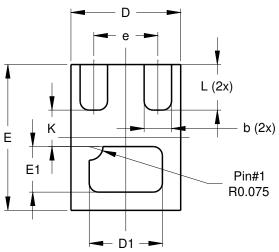




Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

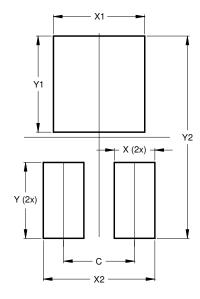




X2-DFN0806-3					
Dim	Min	Max	Тур		
Α	0.375	0.40	0.39		
A 1	0	0.05	0.02		
А3	-	-	0.10		
b	0.10	0.20	0.15		
D	0.55	0.65	0.60		
D1	0.35	0.45	0.40		
Е	0.75	0.85	0.80		
E1	0.20	0.30	0.25		
е	-	-	0.35		
K	1	-	0.20		
L	0.20	0.30	0.25		
All Dimensions in mm					

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.



Dimensions	Value (in mm)		
С	0.350		
Х	0.200		
X1	0.450		
X2	0.550		
Υ	0.375		
Y1	0.475		
Y2	1.000		



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